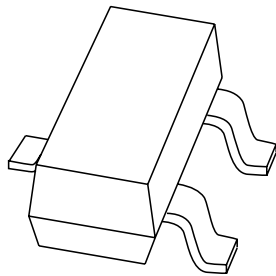


# DATA SHEET



## **PMBTA42** NPN high-voltage transistor

Product specification  
Supersedes data of 1999 Apr 22

2004 Jan 22

# NPN high-voltage transistor

# PMBTA42

### FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

### APPLICATIONS

- Telephony and professional communication equipment.

### DESCRIPTION

NPN high-voltage transistor in a SOT23 plastic package.  
PNP complement: PMBTA92.

### MARKING

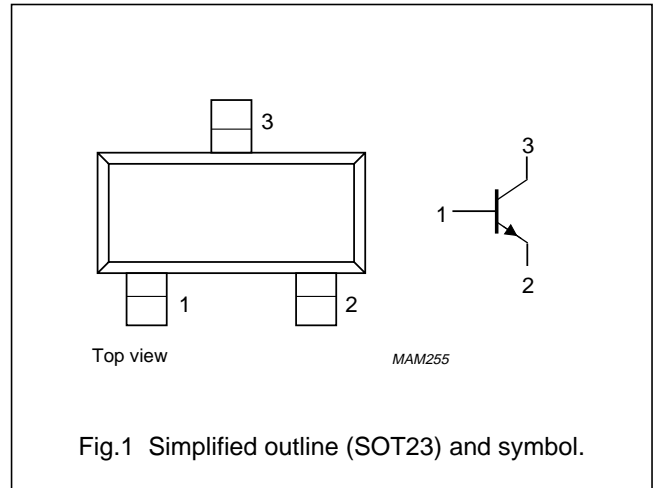
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBTA42	*1D

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBTA42	-	plastic surface mounted package; 3 leads	SOT23

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	300	V
$V_{CEO}$	collector-emitter voltage	open base	-	300	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
$I_C$	collector current (DC)		-	100	mA
$I_{CM}$	peak collector current		-	200	mA
$I_{BM}$	peak base current		-	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	-	250	mW
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		-	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

### Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN high-voltage transistor

## PMBTA42

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = 200\text{ V}$	–	100	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0$ ; $V_{EB} = 6\text{ V}$	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 30\text{ mA}$	25 40 40	– – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 20\text{ mA}$ ; $I_B = 2\text{ mA}$	–	500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 20\text{ mA}$ ; $I_B = 2\text{ mA}$	–	900	mV
$C_{re}$	feedback capacitance	$I_C = I_c = 0$ ; $V_{CB} = 20\text{ V}$ ; $f = 1\text{ MHz}$	–	3	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}$ ; $V_{CE} = 20\text{ V}$ ; $f = 100\text{ MHz}$	50	–	MHz

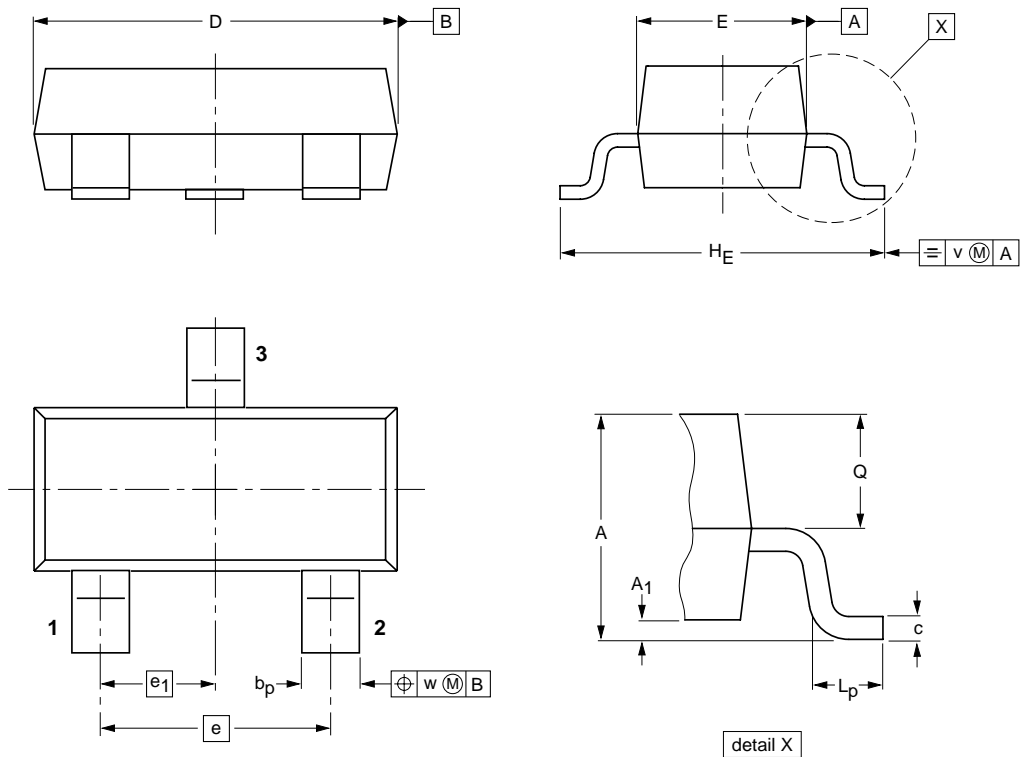
NPN high-voltage transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

## NPN high-voltage transistor

PMBTA42

## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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